

Fan Ren

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

545 papers	17,361 citations	63 h-index	112 g-index
583 ext. papers	19,353 ext. citations	3.3 avg, IF	6.69 L-index

#	Paper	IF	Citations
545	Digital biosensor for human cerebrospinal fluid detection with single-use sensing strips. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2022 , 40, 023202	1.3	1
544	Rapid SARS-CoV-2 diagnosis using disposable strips and a metal-oxide-semiconductor field-effect transistor platform. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2022 , 40, 023204	1.3	3
543	Variable temperature probing of minority carrier transport and optical properties in p-Ga ₂ O ₃ . <i>APL Materials</i> , 2022 , 10, 031106	5.7	2
542	Deep level defect states in α -Ga ₂ O ₃ crystals and films: Impact on device performance. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022 , 40, 020804	2.9	11
541	Exfoliated and bulk α -gallium oxide electronic and photonic devices 2022 , 1, 100001		0
540	Thermo-mechanical aspects of gamma irradiation effects on GaN HEMTs. <i>Applied Physics Letters</i> , 2022 , 120, 124101	3.4	4
539	Growth and characterization of (Sc ₂ O ₃) _x (Ga ₂ O ₃) _{1-x} by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022 , 40, 043403	2.9	1
538	Thermal effects in Ga ₂ O ₃ rectifiers and MOSFETs borrowing from GaN 2022 , 441-467		
537	Temperature dependence of cathodoluminescence emission in irradiated Si-doped α -Ga ₂ O ₃ . <i>AIP Advances</i> , 2021 , 11, 125014	1.5	3
536	Thermal Stability of Transparent ITO/n-Ga ₂ O ₃ /n ⁺ -Ga ₂ O ₃ /ITO Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 115005	2	0
535	Al Composition Dependence of Band Offsets for SiO ₂ on α -(Al _x Ga _{1-x}) ₂ O ₃ . <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 113007	2	1
534	1 GeV proton damage in α -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1
533	Artificial Neuron and Synapse Devices Based on 2D Materials. <i>Small</i> , 2021 , 17, e2100640	11	17
532	Vertical α -Ga ₂ O ₃ Schottky rectifiers with 750 V reverse breakdown voltage at 600 K. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 305103	3	4
531	Fast SARS-CoV-2 virus detection using disposable cartridge strips and a semiconductor-based biosensor platform. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2021 , 39, 033202	1.3	6
530	Review Radiation Damage in Wide and Ultra-Wide Bandgap Semiconductors. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 055008	2	19
529	Experimental estimation of electron-hole pair creation energy in α -Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2021 , 118, 202106	3.4	8

528	Electron beam probing of non-equilibrium carrier dynamics in 18 MeV alpha particle- and 10 MeV proton-irradiated Si-doped EGa_2O_3 Schottky rectifiers. <i>Applied Physics Letters</i> , 2021 , 118, 202105	3.4	5
527	Neuromorphic Devices: Artificial Neuron and Synapse Devices Based on 2D Materials (Small 20/2021). <i>Small</i> , 2021 , 17, 2170092	11	
526	A Review: Microstructural and Phase Evolution in Alloys during Extended Plastic Deformation. <i>Jom</i> , 2021 , 73, 2212-2224	2.1	1
525	Crystal orientation dependence of deep level spectra in proton irradiated bulk EGa_2O_3 . <i>Journal of Applied Physics</i> , 2021 , 130, 035701	2.5	4
524	Qualitative Analysis of Remineralization Capabilities of Bioactive Glass (NovaMin) and Fluoride on Hydroxyapatite (HA) Discs: An In Vitro Study. <i>Materials</i> , 2021 , 14,	3.5	3
523	Novel Coatings to Minimize Corrosion of Titanium in Oral Biofilm. <i>Materials</i> , 2021 , 14,	3.5	4
522	Design of Ga_2O_3 modulation doped field effect transistors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 023412	2.9	4
521	Review Opportunities in Single Event Effects in Radiation-Exposed SiC and GaN Power Electronics. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 075004	2	5
520	OH-Si complex in hydrogenated n-type $\text{EGa}_2\text{O}_3\text{:Si}$. <i>Applied Physics Letters</i> , 2021 , 119, 062109	3.4	6
519	Nanostructured Surfaces to Promote Osteoblast Proliferation and Minimize Bacterial Adhesion on Titanium. <i>Materials</i> , 2021 , 14,	3.5	3
518	Temperature dependent performance of ITO Schottky contacts on EGa_2O_3 . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 053405	2.9	6
517	On the nature of photosensitivity gain in Ga_2O_3 Schottky diode detectors: Effects of hole trapping by deep acceptors. <i>Journal of Alloys and Compounds</i> , 2021 , 879, 160394	5.7	6
516	Nitrogen ion-implanted resistive regions for edge termination of vertical Ga_2O_3 rectifiers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 063405	2.9	3
515	Diffusion of dopants and impurities in EGa_2O_3 . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 060801	2.9	8
514	Effect of probe geometry during measurement of >100 A Ga_2O_3 vertical rectifiers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 013406	2.9	11
513	Titanium Corrosion in Peri-Implantitis. <i>Materials</i> , 2020 , 13,	3.5	1
512	Hydroxyapatite Formation on Coated Titanium Implants Submerged in Simulated Body Fluid. <i>Materials</i> , 2020 , 13,	3.5	3
511	Band offset determination for amorphous Al_2O_3 deposited on bulk AlN and atomic-layer epitaxial AlN on sapphire. <i>Applied Physics Letters</i> , 2020 , 117, 182103	3.4	1

510	Photosensitivity of Ga ₂ O ₃ Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , 2020 , 8, 111105	5.7	13
509	Effect of Electron Injection on Minority Carrier Transport in 10 MeV Proton Irradiated $\text{In}_{0.5}\text{Ga}_{0.5}\text{O}_3$ Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 045018	2	6
508	Alpha Particle Irradiation of High Aluminum Content AlGaN Polarization Doped Field Effect Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 035008	2	2
507	AlGaN/GaN heterostructure based Pt nanonetwork Schottky diode with water-blocking layer. <i>Sensors and Actuators B: Chemical</i> , 2020 , 317, 128234	8.5	2
506	In Situ Transmission Electron Microscopy Observations of Forward Bias Degradation of Vertical Geometry $\text{In}_{0.5}\text{Ga}_{0.5}\text{O}_3$ Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 055008	2	3
505	Annealing Effects on the Band Alignment of ALD SiO ₂ on (In _x Ga _{1-x}) ₂ O ₃ for x = 0.25-0.74. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 045001	2	
504	Annealing and N Plasma Treatment to Minimize Corrosion of SiC-Coated Glass-Ceramics. <i>Materials</i> , 2020 , 13,	3.5	2
503	Novel Coatings to Minimize Bacterial Adhesion and Promote Osteoblast Activity for Titanium Implants. <i>Journal of Functional Biomaterials</i> , 2020 , 11,	4.8	7
502	Novel Coating to Minimize Corrosion of Glass-Ceramics for Dental Applications. <i>Materials</i> , 2020 , 13,	3.5	7
501	Dissolution activation energy of a fluorapatite glass-ceramic veneer for dental applications. <i>Materials Science and Engineering C</i> , 2020 , 111, 110802	8.3	2
500	Asymmetrical Contact Geometry to Reduce Forward-Bias Degradation in $\text{In}_{0.5}\text{Ga}_{0.5}\text{O}_3$ Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 035007	2	5
499	Changes in band alignment during annealing at 600 °C of ALD Al ₂ O ₃ on (In _x Ga _{1-x}) ₂ O ₃ for x = 0.25-0.74. <i>Journal of Applied Physics</i> , 2020 , 127, 105701	2.5	3
498	In Situ Observation of $\text{In}_{0.5}\text{Ga}_{0.5}\text{O}_3$ Schottky Diode Failure Under Forward Biasing Condition. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3056-3061	2.9	7
497	Plasma etching of wide bandgap and ultrawide bandgap semiconductors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 020802	2.9	13
496	Pulsed fast reactor neutron irradiation effects in Si doped n-type $\text{In}_{0.5}\text{Ga}_{0.5}\text{O}_3$. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 274001	3	13
495	Nanosensor networks for health-care applications 2020 , 405-417		2
494	Diodes 1. <i>Springer Series in Materials Science</i> , 2020 , 661-688	0.9	
493	Opportunities and Challenges in MOCVD of $\text{In}_{0.5}\text{Ga}_{0.5}\text{O}_3$ for Power Electronic Devices. <i>Selected Topics in Electornics and Systems</i> , 2020 , 127-144	0	

492	PrefaceISS Focus Issue on Gallium Oxide Based Materials and Devices II. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 060001	2	0
491	Anti-Bacterial Properties and Biocompatibility of Novel SiC Coating for Dental Ceramic. <i>Journal of Functional Biomaterials</i> , 2020 , 11,	4.8	11
490	Design and implementation of floating field ring edge termination on vertical geometry EGa2O3 rectifiers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 063414	2.9	1
489	PrefaceISS Focus Issue on Solid-State Materials and Devices for Biological and Medical Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 110001	2	
488	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in EGa2O3 vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 495108	3	11
487	ReviewOpportunities for Rapid, Sensitive Detection of Troponin and Cerebral Spinal Fluid Using Semiconductor Sensors. <i>Journal of the Electrochemical Society</i> , 2020 , 167, 037507	3.9	4
486	A Two-Electrode, Double-Pulsed Sensor Readout Circuit for Cardiac Troponin I Measurement. <i>IEEE Transactions on Biomedical Circuits and Systems</i> , 2020 , 14, 1362-1370	5.1	3
485	Impact of electron injection on carrier transport and recombination in unintentionally doped GaN. <i>Journal of Applied Physics</i> , 2020 , 128, 085702	2.5	5
484	Demonstration of a SiC Protective Coating for Titanium Implants. <i>Materials</i> , 2020 , 13,	3.5	10
483	Rapid Electrochemical Detection for SARS-CoV-2 and Cardiac Troponin I Using Low-Cost, Disposable and Modular Biosensor System 2020 ,		4
482	High temperature operation to 500 °C of AlGaIn graded polarization-doped field-effect transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2020 , 38, 033202	1.3	1
481	Antibacterial Properties of Charged TiN Surfaces for Dental Implant Application. <i>ChemistrySelect</i> , 2019 , 4, 9185-9189	1.8	6
480	Forward bias degradation and thermal simulations of vertical geometry EGa2O3 Schottky rectifiers. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2019 , 37, 061205	1.3	11
479	Band Offsets of Insulating & Semiconducting Oxides on (Al _x Ga _{1-x})O ₃ . <i>ECS Transactions</i> , 2019 , 92, 79-88	1	5
478	Diffusion of implanted Ge and Sn in EGa2O3. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2019 , 37, 051204	1.3	16
477	Effect of thermal annealing for W/EGa2O3 Schottky diodes up to 600 °C. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2019 , 37, 061201	1.3	10
476	Radiation damage effects in Ga2O3 materials and devices. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 10-24	1	90
475	Electron injection-induced effects in Si-doped EGa2O3. <i>AIP Advances</i> , 2019 , 9, 015127	1.5	11

474	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski $\text{E}\text{Ga}_2\text{O}_3$ (Mg). <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3019-Q3023	2	25
473	Device processing and junction formation needs for ultra-high power Ga_2O_3 electronics. <i>MRS Communications</i> , 2019 , 9, 77-87	2.7	11
472	Switching Behavior and Forward Bias Degradation of 700V, 0.2A, $\text{E}\text{Ga}_2\text{O}_3$ Vertical Geometry Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3028-Q3033	2	12
471	Implementation of a 900V Switching Circuit for High Breakdown Voltage $\text{E}\text{Ga}_2\text{O}_3$ Schottky Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3229-Q3234	2	7
470	Fast Cerebrospinal Fluid Detection Using Inexpensive Modular Packaging with Disposable Testing Strips. <i>Journal of the Electrochemical Society</i> , 2019 , 166, B708-B712	3.9	5
469	Vertical geometry 33.2 A, 4.8 MW cm^2 Ga_2O_3 field-plated Schottky rectifier arrays. <i>Applied Physics Letters</i> , 2019 , 114, 232106	3.4	26
468	Defects at the surface of $\text{E}\text{Ga}_2\text{O}_3$ produced by Ar plasma exposure. <i>APL Materials</i> , 2019 , 7, 061102	5.7	25
467	Will surface effects dominate in quasi-two-dimensional gallium oxide for electronic and photonic devices?. <i>Nanoscale Horizons</i> , 2019 , 4, 1251-1255	10.8	8
466	Comparison of Dual-Stack Dielectric Field Plates on $\text{E}\text{Ga}_2\text{O}_3$ Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3221-Q3225	2	16
465	Thermoreflectance Temperature Mapping of Ga_2O_3 Schottky Barrier Diodes. <i>ECS Transactions</i> , 2019 , 89, 3-7	1	3
464	Demonstration of SiO/SiC based protective coating for dental ceramic prostheses. <i>Journal of the American Ceramic Society</i> , 2019 , 102, 6591-6599	3.8	7
463	Operation Up to 500 $^{\circ}\text{C}$ of $\text{Al}_{0.85}\text{Ga}_{0.15}\text{N}/\text{Al}_{0.7}\text{Ga}_{0.3}\text{N}$ High Electron Mobility Transistors. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 7, 444-452	2.3	27
462	Damage Recovery and Dopant Diffusion in Si and Sn Ion Implanted $\text{E}\text{Ga}_2\text{O}_3$. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3133-Q3139	2	20
461	Reverse Breakdown in Large Area, Field-Plated, Vertical $\text{E}\text{Ga}_2\text{O}_3$ Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3159-Q3164	2	16
460	Deep traps and persistent photocapacitance in $(\text{Al}_{0.14}\text{Ga}_{0.86})_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterojunctions. <i>Journal of Applied Physics</i> , 2019 , 125, 095702	2.5	1
459	Heterojunction Bipolar Transistor: 2D Material-Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification (Adv. Electron. Mater. 3/2019). <i>Advanced Electronic Materials</i> , 2019 , 5, 1970015	6.4	1
458	Valence and Conduction Band Offsets for InN and III-Nitride Ternary Alloys on (001) Bulk $\text{E}\text{Ga}_2\text{O}_3$. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3154-Q3158	2	9
457	Thermal Simulations of High Current $\text{E}\text{Ga}_2\text{O}_3$ Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3195-Q3201	2	17

456	60Co Gamma Ray Damage in Homoepitaxial EgGa_2O_3 Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3041-Q3045	2	10
455	Valence band offsets for ALD SiO_2 and Al_2O_3 on $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.25$ – 0.74 . <i>APL Materials</i> , 2019 , 7, 071115	5.7	9
454	The role of annealing ambient on diffusion of implanted Si in EgGa_2O_3 . <i>AIP Advances</i> , 2019 , 9, 085111	1.5	18
453	Hydrogen plasma treatment of EgGa_2O_3 : Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , 2019 , 115, 032101	3.4	29
452	Band Alignment of Atomic Layer Deposited SiO_2 and Al_2O_3 on $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.2$ – 0.65 . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P351-P356	2	8
451	A Reconfigurable, Pulse-shaping Potentiometric Readout System for Bio-Sensing Transistors. <i>Annual International Conference of the IEEE Engineering in Medicine and Biology Society IEEE Engineering in Medicine and Biology Society Annual International Conference</i> , 2019 , 2019, 5761-5764	0.9	2
450	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of EgGa_2O_3 . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P661-P666	2	4
449	Valence- and Conduction-Band Offsets for Atomic-Layer-Deposited Al_2O_3 on (010) $(\text{Al}_{0.14}\text{Ga}_{0.86})_2\text{O}_3$. <i>Journal of Electronic Materials</i> , 2019 , 48, 1568-1573	1.9	19
448	Impact of Electron Injection and Temperature on Minority Carrier Transport in Alpha-Irradiated EgGa_2O_3 Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3050-Q3053	2	8
447	Comprehensive analysis of laserscanner validity used for measurement of wear. <i>Journal of Oral Rehabilitation</i> , 2019 , 46, 503-510	3.4	2
446	Effect of Annealing on the Band Alignment of ALD SiO_2 on $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.2$ – 0.65 . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P751-P756	2	4
445	Annealing of Proton and Alpha Particle Damage in Au-W/ EgGa_2O_3 Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P799-P804	2	1
444	Opportunities and Challenges in MOCVD of EgGa_2O_3 for Power Electronic Devices. <i>International Journal of High Speed Electronics and Systems</i> , 2019 , 28, 1940007	0.5	4
443	Optimization of Edge Termination Techniques for EgGa_2O_3 Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q234-Q239	2	10
442	Temperature-Dependent Electrical Characteristics of EgGa_2O_3 Diodes with W Schottky Contacts up to 500°C . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3007-Q3012	2	28
441	Valence and conduction band offsets for sputtered AZO and ITO on (010) $(\text{Al}_{0.14}\text{Ga}_{0.86})_2\text{O}_3$. <i>Semiconductor Science and Technology</i> , 2019 , 34, 025006	1.8	6
440	2D Material-Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800745	6.4	16
439	Defect States Determining Dynamic Trapping-Detrapping in EgGa_2O_3 Field-Effect Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3013-Q3018	2	19

438	Dynamic Switching Characteristics of 1 A Forward Current β -Ga ₂ O ₃ Rectifiers. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 7, 57-61	2.3	20
437	Effect of Deposition Method on Valence Band Offsets of SiO ₂ and Al ₂ O ₃ on (Al _{0.14} Ga _{0.86}) ₂ O ₃ . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3001-Q3006	2	9
436	Band alignments of dielectrics on (1101) β -Ga ₂ O ₃ 2019 , 287-311		2
435	Moisture Insensitive PMMA Coated Pt-AlGa _n /Ga _n Diode Hydrogen Sensor and Its Thermal Stability. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q3009-Q3013	2	7
434	Trapping Phenomena in InAlN/GaN High Electron Mobility Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q1-Q7	2	9
433	Point defect induced degradation of electrical properties of Ga ₂ O ₃ by 10 MeV proton damage. <i>Applied Physics Letters</i> , 2018 , 112, 032107	3.4	72
432	A review of Ga ₂ O ₃ materials, processing, and devices. <i>Applied Physics Reviews</i> , 2018 , 5, 011301	17.3	1114
431	10 MeV proton damage in β -Ga ₂ O ₃ Schottky rectifiers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 011206	1.3	24
430	Effects of fluorine incorporation into β -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2018 , 123, 165706	2.5	16
429	Effect of 1.5 MeV electron irradiation on β -Ga ₂ O ₃ carrier lifetime and diffusion length. <i>Applied Physics Letters</i> , 2018 , 112, 082104	3.4	37
428	AlGa _n /Ga _n Heterostructure Based Schottky Diode Sensors with ZnO Nanorods for Environmental Ammonia Monitoring Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q3020-Q3024	3.24	14
427	Randomized clinical study of wear of enamel antagonists against polished monolithic zirconia crowns. <i>Journal of Dentistry</i> , 2018 , 68, 19-27	4.8	46
426	A comparative study of wet etching and contacts on (2101) and (010) oriented β -Ga ₂ O ₃ . <i>Journal of Alloys and Compounds</i> , 2018 , 731, 118-125	5.7	35
425	Novel Testing for Corrosion of Glass-Ceramics for Dental Applications. <i>Journal of Dental Research</i> , 2018 , 97, 296-302	8.1	6
424	Effect of alpha-particle irradiation dose on SiN _x /AlGa _n /Ga _n metal-insulator semiconductor high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 041203	1.3	4
423	Zika virus detection using antibody-immobilized disposable cover glass and AlGa _n /Ga _n high electron mobility transistors. <i>Applied Physics Letters</i> , 2018 , 113, 032101	3.4	18
422	Diffusion length of non-equilibrium minority charge carriers in β -Ga ₂ O ₃ measured by electron beam induced current. <i>Journal of Applied Physics</i> , 2018 , 123, 185704	2.5	37
421	Eighteen mega-electron-volt alpha-particle damage in homoepitaxial β -Ga ₂ O ₃ Schottky rectifiers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 031205	1.3	13

420	Ga2O3 Schottky rectifiers with 1 ampere forward current, 650 V reverse breakdown and 26.5 MW.cm-2 figure-of-merit. <i>AIP Advances</i> , 2018 , 8, 055026	1.5	51
419	Vertical Geometry, 2-A Forward Current Ga2O3 Schottky Rectifiers on Bulk Ga2O3 Substrates. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2790-2796	2.9	30
418	Perspective: Ga2O3 for ultra-high power rectifiers and MOSFETS. <i>Journal of Applied Physics</i> , 2018 , 124, 220901	2.5	245
417	Band alignment of atomic layer deposited SiO2 on (010) (Al0.14Ga0.86)2O3. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2018 , 36, 061207	1.3	15
416	Band Offsets for Atomic Layer Deposited HfSiO4 on (Al0.14Ga0.86)2O3. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P519-P523	2	8
415	Effect of surface treatments on electrical properties of β -Ga2O3. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2018 , 36, 061201	1.3	30
414	Electrical properties of bulk semi-insulating β -Ga2O3 (Fe). <i>Applied Physics Letters</i> , 2018 , 113, 142102	3.4	59
413	Valence band offsets for CuI on (-201) bulk Ga2O3 and epitaxial (010) (Al0.14Ga0.86)2O3. <i>Applied Physics Letters</i> , 2018 , 113, 182101	3.4	12
412	Hole traps and persistent photocapacitance in proton irradiated β -Ga2O3 films doped with Si. <i>APL Materials</i> , 2018 , 6, 096102	5.7	50
411	Effect of proton irradiation energy on SiNx/AlGaN/GaN metal-insulator semiconductor high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2018 , 36, 052202	1.3	11
410	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated β -Ga2O3. <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
409	2300V Reverse Breakdown Voltage Ga2O3Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q92-Q96	2	116
408	Hydrogen Sensing Characteristics of Pt Schottky Diodes on () and (010) Ga2O3Single Crystals. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q3180-Q3182	2	15
407	Current relaxation analysis in AlGaN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2017 , 35, 011207	1.3	7
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